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Valerie BOUSQUET, et al.

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## U.S. PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Document Number	Date	Name	Class/ Subclass	(If appropriate) Filing Date

## FOREIGN PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation Yes	No

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

Ref. Desig.	Examiner's Initials	
		Japanese Office Action dated July 10, 2009.
		Selkoh Yoshida, "Photoluminescence measurement of InGaN and GaN grown by a gas-source molecular-beam epitaxy method", J. Appl. Phys., Vol. 81, No. 12, pp. 7966-7969 (1997).
		N. Grandjean, et al., "Real time control of In <sub>x</sub> Ga <sub>1-x</sub> N molecular beam epitaxy growth", Appl. Phys. Lett., Vol. 72, No. 9, pp. 1078-1080 (1998).

DDJ/ACC:vrj

Examiner: /Asok Sarkar/

Date Considered: 08/25/2009

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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /A.S./